

App. Serial No 10/539,280  
Docket No.: BE020045US

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In the Claims:

SEP 07 2007

Please amend claims 1, 4 and 6-8 as indicated below. This listing of claims replaces all prior versions.

1. *(Currently amended)* A method of manufacturing a semiconductor device with a semiconductor body, the semiconductor device including and a substrate and comprising, at least one semiconductor element, the semiconductor device that is equipped with at least one connection region and connected to a superjacent strip-shaped connection conductor connected to the connection region, the connection region and the superjacent strip-shaped connection conductor are both being recessed in a dielectric layer, and the method comprising:

providing a first material in a dielectric region of a first material is provided on the semiconductor body at the a location of the connection region to be formed, the first material being made of an organic material and the first material having a decomposition temperature;

coating the dielectric region is coated with [[a]] the dielectric layer, the dielectric layer being made of a second material having a decomposition temperature that is higher than the decomposition temperature of the first material; that differs from the first material,

removing the first material by heating the semiconductor device to a temperature that is above the decomposition temperature of the first material yet below the decomposition temperature of the second material;

after removing the first material, etching the said dielectric layer is provided, at the location of the strip-shaped connection conductor to be formed, with to form a strip-shaped recess viewed in projection, that overlaps the dielectric region and extends up to said the dielectric region;[[.]])

and after the formation of the strip-shaped recess and the removal of the dielectric region,

forming the connection region is formed by depositing an electroconductive material in a space obtained by the removal of the first material; dielectric region, and

App. Serial No 10/539,280  
Docket No.: BE020045US

forming the superjacent strip-shaped connection conductor is formed by  
depositing an electroconductive material in the strip-shaped recess, characterized in that  
~~for the first material use is made of an organic material, and~~  
~~for the second material use is made of a material having a higher decomposition~~  
~~temperature than the organic material, and~~  
~~the dielectric region is removed by heating at a temperature above the~~  
~~decomposition temperature of the organic material yet below the decomposition~~  
~~temperature of the second material.~~

2. (*Previously presented*) A method as claimed in claim 1, characterized in that  
a photoresist is used as the first material, and  
a dielectric resin having a higher decomposition temperature than the photoresist  
is used as the second material.
3. (*Previously presented*) A method as claimed in claim 1, characterized in that  
a photoresist is used as the first material, and a liquid glass is used as the second  
material, said liquid glass is converted to solid glass by heating.
4. (*Currently amended*) A method as claimed in claim 2, characterized in that  
the dielectric region first material is removed during a thermal treatment of the  
semiconductor body wherein the liquid glass is converted to solid glass.
5. (*Previously presented*) A method as claimed in claim 1, characterized in that  
the first material as well as the second material are applied in liquid state to the  
semiconductor body with a centrifuging process.
6. (*Currently amended*) A method as claimed in claim 1, characterized in that  
the dielectric region is formed by applying a further dielectric layer, covering part  
of the further dielectric layer with above which a mask, and is provided removing the part  
of ~~outside which~~ the further dielectric layer not covered by the mask is removed by  
means of etching;[[,]] and

App. Serial No 10/539,280  
Docket No.: BE020045US

the dielectric layer, after deposition, is covered with a mask which is provided with having an aperture at the a location of where the strip-shaped recess will be formed, after which the strip-shaped recess is formed by means of etching.

7. (*Currently amended*) A method as claimed in claim 1, characterized in that after removal of the first material dielectric region and after formation of the strip-shaped recess, yet before deposition of the conductive material, the semiconductor body is cleaned.

8. (*Currently amended*) A method as claimed in claim 1, characterized in that copper is used as the electroconductive material, and

prior to the deposition of the copper, an electroconductive layer is deposited, at the location of the connection region to be being formed on the electroconductive layer, said electroconductive layer forms a barrier for copper.

9. (*Previously presented*) A method as claimed in claim 8, characterized in that the electroconductive layer is applied by means of a physical vapor deposition process, and

the copper is provided by means of an electroplating process.

10. (*Previously presented*) A semiconductor device obtained by the method of claim 1.